

1. Product profile

1.1 General description

Planar passivated SCR (Silicon Controlled Rectifier) in a SOT78 plastic package.

1.2 Features and benefits

- High reliability
- High surge current capability
- High thermal cycling performance

1.3 Applications

- Ignition circuits
- Motor control
- Protection Circuits
- Static switching

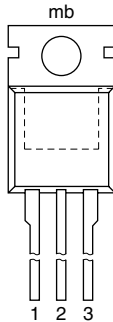
1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	500	V
$I_{\text{T(AV)}}$	average on-state current	half sine wave; $T_{\text{mb}} \leq 109\text{ °C}$; see Figure 3	-	-	7.5	A
$I_{\text{T(RMS)}}$	RMS on-state current	half sine wave; $T_{\text{mb}} \leq 109\text{ °C}$; see Figure 1 ; see Figure 2	-	-	12	A
Static characteristics						
I_{GT}	gate trigger current	$V_{\text{D}} = 12\text{ V}$; $T_{\text{j}} = 25\text{ °C}$; $I_{\text{T}} = 100\text{ mA}$; see Figure 8	-	2	15	mA

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
3	G	gate		
mb	mb	anode		
SOT78 (TO-220AB; SC-46)				

3. Ordering information

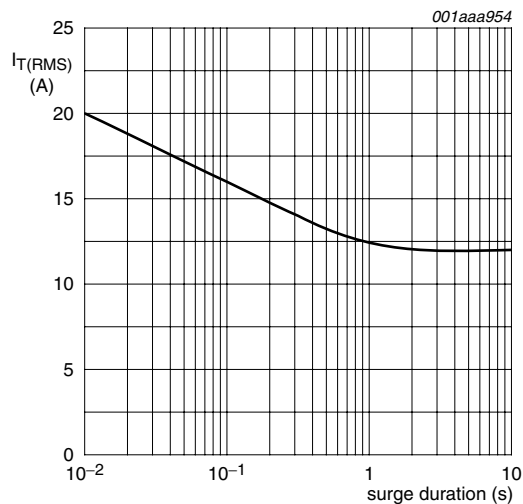
Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BT151-500C	TO-220AB; SC-46	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	500	V
V_{RRM}	repetitive peak reverse voltage		-	500	V
$I_{\text{T(AV)}}$	average on-state current	half sine wave; $T_{\text{mb}} \leq 109\text{ °C}$; see Figure 3	-	7.5	A
$I_{\text{T(RMS)}}$	RMS on-state current	half sine wave; $T_{\text{mb}} \leq 109\text{ °C}$; see Figure 1 ; see Figure 2	-	12	A
di_{T}/dt	rate of rise of on-state current	$I_{\text{T}} = 20\text{ A}$; $I_{\text{G}} = 50\text{ mA}$; $di_{\text{G}}/dt = 50\text{ mA}/\mu\text{s}$	-	50	A/ μs
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
T_{stg}	storage temperature		-40	150	°C
T_{j}	junction temperature		-	125	°C
I_{TSM}	non-repetitive peak on-state current	half sine wave; $t_{\text{p}} = 8.3\text{ ms}$; $T_{\text{j(init)}} = 25\text{ °C}$	-	132	A
		half sine wave; $t_{\text{p}} = 10\text{ ms}$; $T_{\text{j(init)}} = 25\text{ °C}$; see Figure 4 ; see Figure 5	-	120	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ ms}$; sine-wave pulse	-	72	A ² s
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.5	W
V_{RGM}	peak reverse gate voltage		-	5	V



$$f = 50\text{Hz}; T_{\text{mb}} = 109\text{ °C}$$

Fig 1. RMS on-state current as a function of surge duration; maximum values

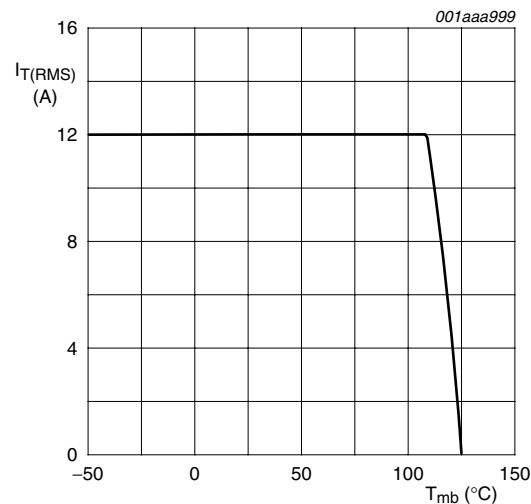


Fig 2. RMS on-state current as a function of mounting base temperature; maximum values

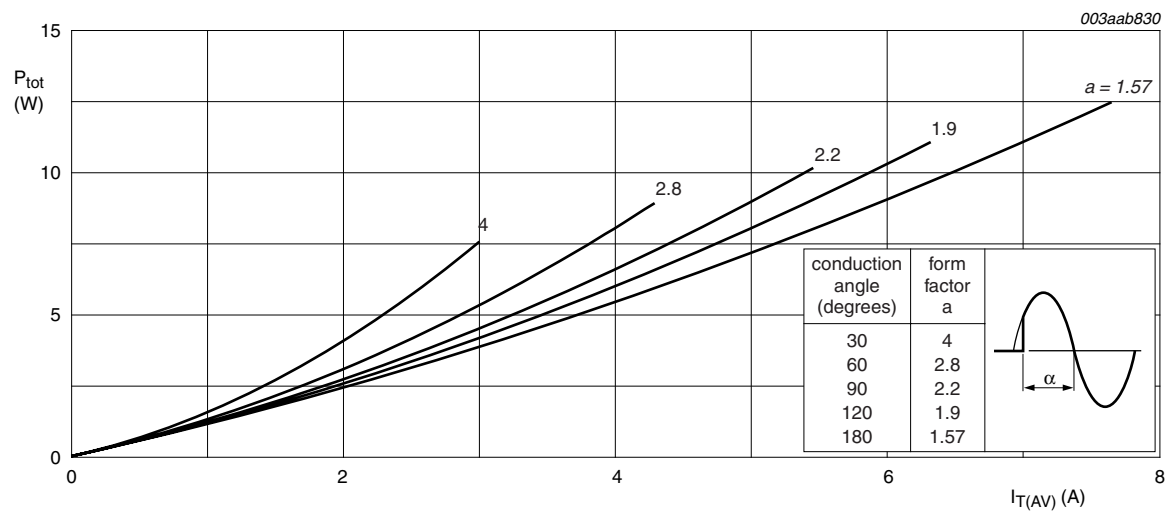
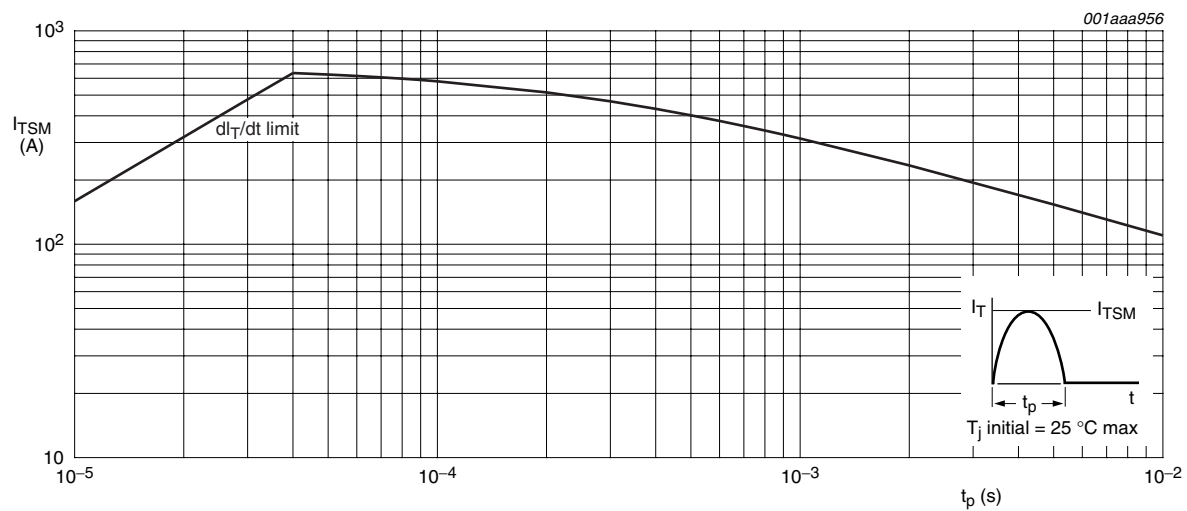


Fig 3. Total power dissipation as a function of average on-state current; maximum values



$$t_p = 10 \text{ ms}$$

Fig 4. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

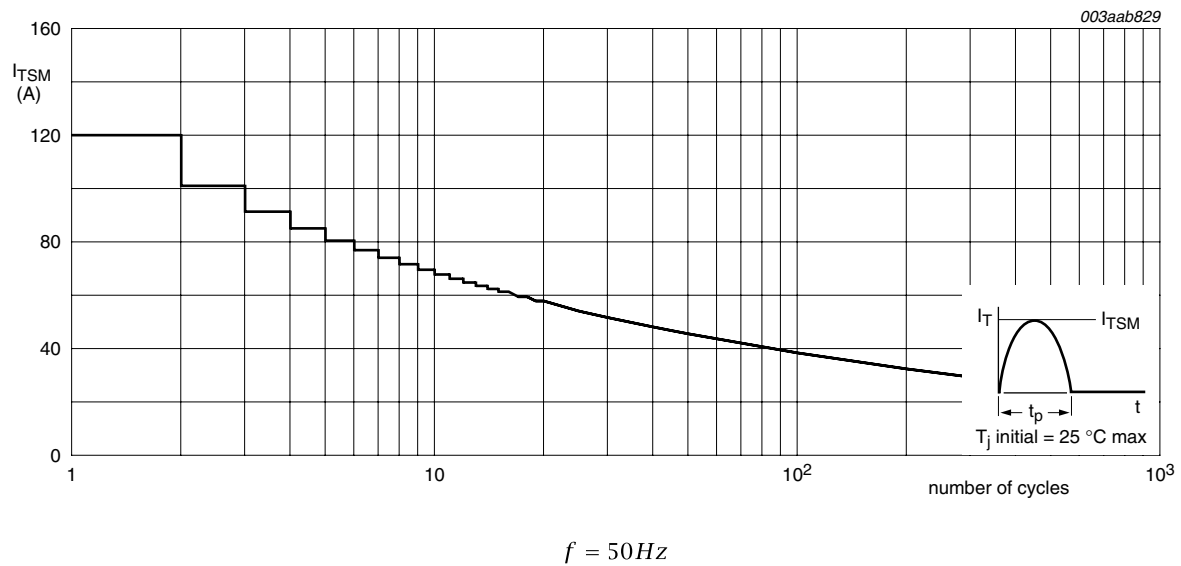


Fig 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 6	-	-	1.3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air		-	60	-	K/W

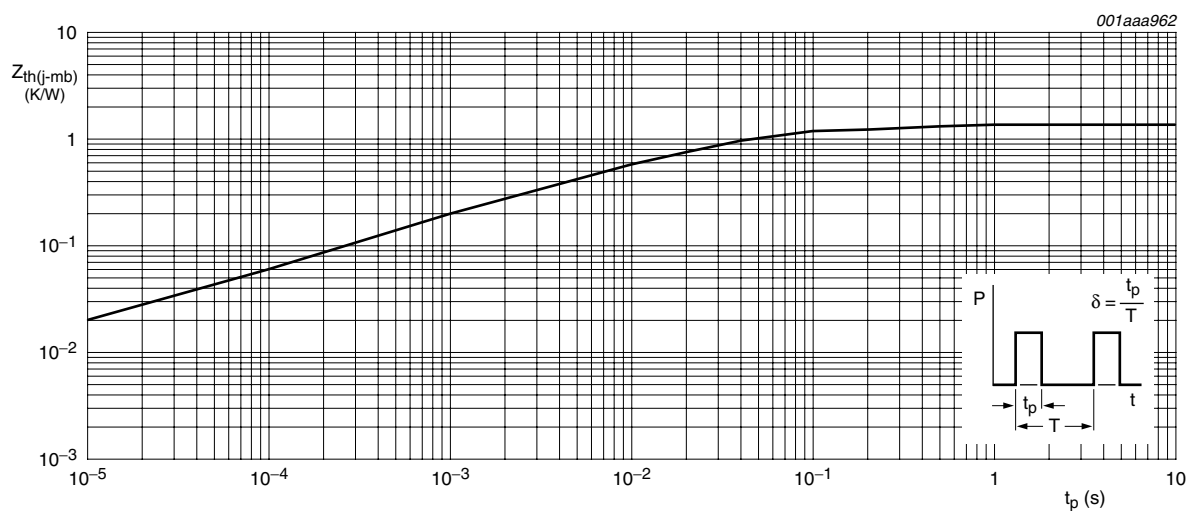


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; $I_T = 100\text{ mA}$; see Figure 8	-	2	15	mA
I_L	latching current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; see Figure 9	-	10	40	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; see Figure 10	-	7	20	mA
V_T	on-state voltage	$I_T = 23\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; see Figure 11	-	1.4	1.75	V
V_{GT}	gate trigger voltage	$I_T = 100\text{ mA}$; $V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; see Figure 12	-	0.6	1.5	V
		$I_T = 100\text{ mA}$; $V_D = 500\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$	0.25	0.4	-	V
I_D	off-state current	$V_D = 500\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
I_R	reverse current	$V_R = 500\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 335\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; exponential waveform; gate open circuit	50	130	-	V/ μs
		$V_{DM} = 335\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $R_{GK} = 100\text{ }\Omega$; exponential waveform; see Figure 7	200	1000	-	V/ μs
t_{gt}	gate-controlled turn-on time	$I_{TM} = 40\text{ A}$; $V_D = 500\text{ V}$; $I_G = 100\text{ mA}$; $dl_G/dt = 5\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^\circ\text{C}$	-	2	-	μs
t_q	commutated turn-off time	$V_{DM} = 335\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{TM} = 20\text{ A}$; $V_R = 25\text{ V}$; $(dl_T/dt)_M = 30\text{ A}/\mu\text{s}$; $dV_D/dt = 50\text{ V}/\mu\text{s}$; $R_{GK} = 100\text{ }\Omega$	-	70	-	μs

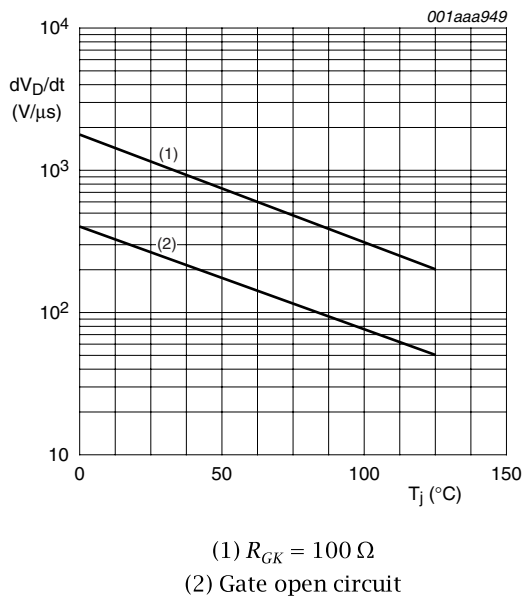


Fig 7. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

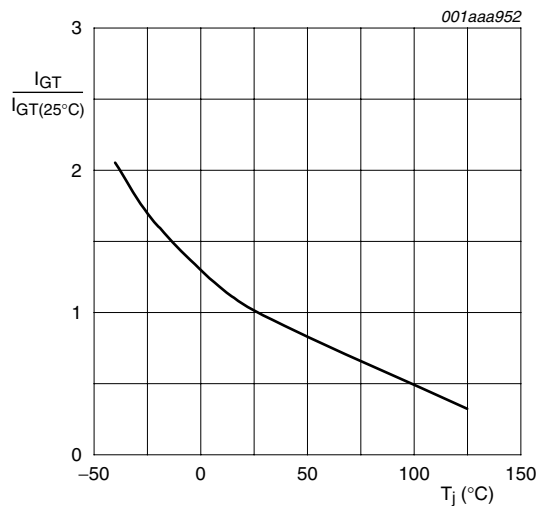


Fig 8. Normalized gate trigger current as a function of junction temperature

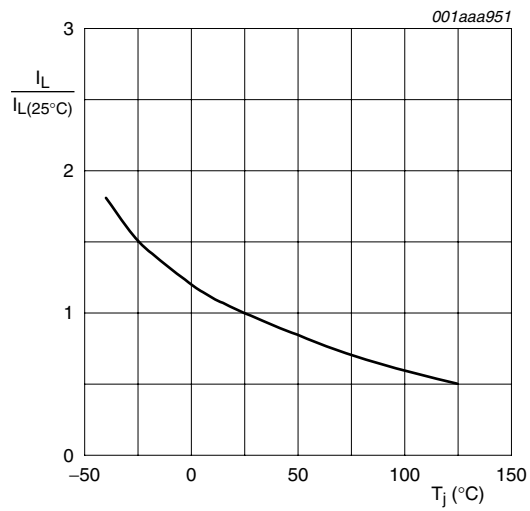


Fig 9. Normalized latching current as a function of junction temperature

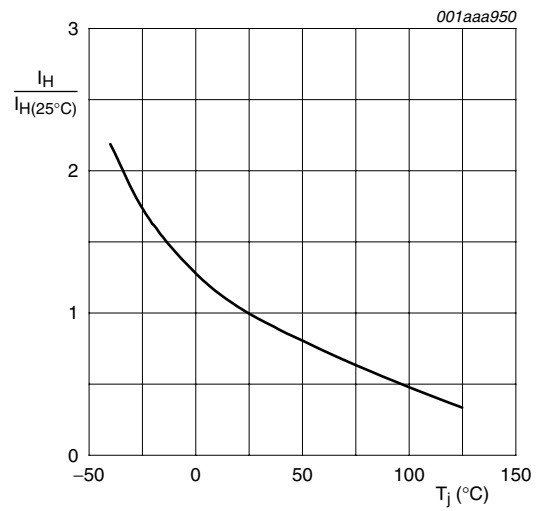
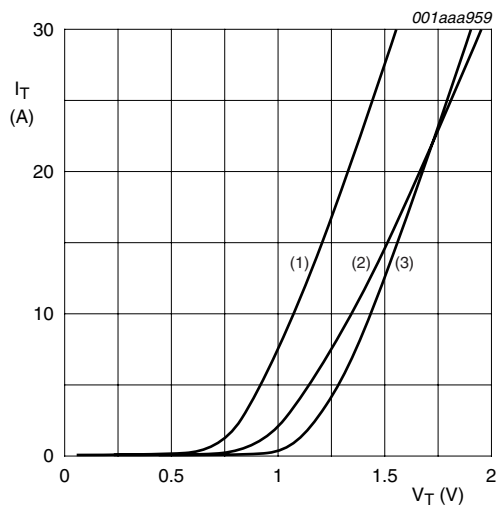


Fig 10. Normalized holding current as a function of junction temperature



- $V_0 = 1.06 \text{ V}; R_s = 0.0304 \Omega$
 (1) $T_j = 150 \text{ }^\circ\text{C}$; typical values
 (2) $T_j = 150 \text{ }^\circ\text{C}$; maximum values
 (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig 11. On-state current as a function of on-state voltage

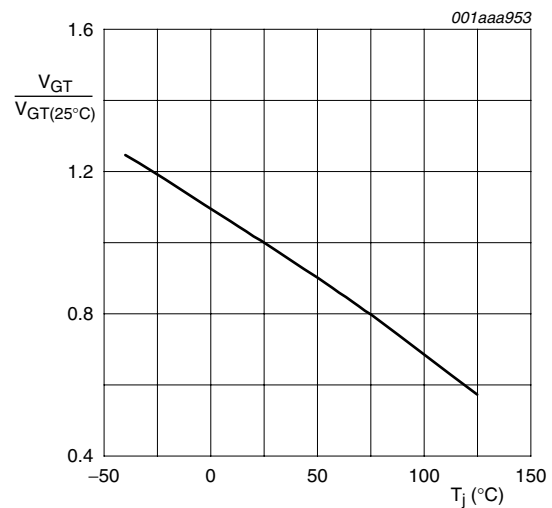
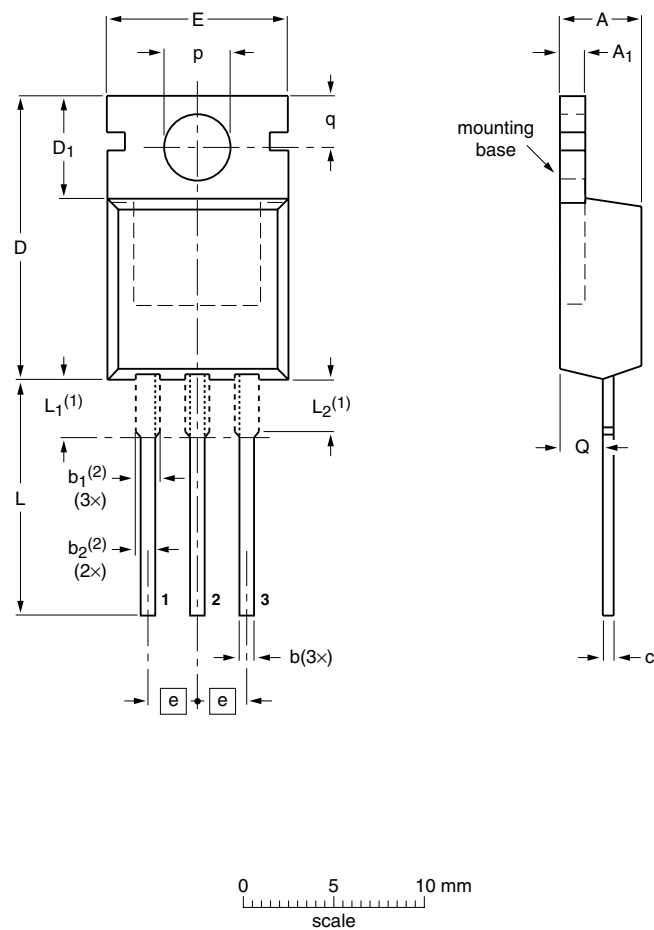


Fig 12. Normalized gate trigger voltage as a function of junction temperature

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (2)	b ₂ (2)	c	D	D ₁	E	e	L	L ₁ (1)	L ₂ (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig 13. Package outline SOT78 (TO-220AB)